

BC327...BC328

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications

These types are subdivided into three groups -16, -25 and -40, according to their DC current gain.



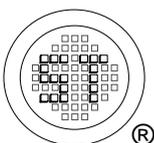
1. Collector 2. Base 3. Emitter
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | BC327 | BC328 | Unit |
|---------------------------|------------|---------------|-------|------------------|
| Collector Base Voltage | $-V_{CBO}$ | 50 | 30 | V |
| Collector Emitter Voltage | $-V_{CEO}$ | 45 | 25 | V |
| Emitter Base Voltage | $-V_{EBO}$ | 5 | | V |
| Collector Current | $-I_C$ | 800 | | mA |
| Peak Collector Current | $-I_{CM}$ | 1 | | A |
| Total Power Dissipation | P_{tot} | 625 | | mW |
| Junction Temperature | T_j | 150 | | $^\circ\text{C}$ |
| Storage Temperature Range | T_S | - 55 to + 150 | | $^\circ\text{C}$ |

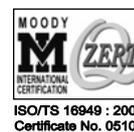
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit | |
|---|----------------|----------------|----------|--------|------------|-----|
| DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$ Current Gain Group at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$ | -16 | h_{FE} | 100 | - | 250 | - |
| | -25 | h_{FE} | 160 | - | 400 | - |
| | -40 | h_{FE} | 250 | - | 630 | - |
| | -16 | h_{FE} | 60 | - | - | - |
| | -25 | h_{FE} | 100 | - | - | - |
| | -40 | h_{FE} | 170 | - | - | - |
| Collector Base Cutoff Current at $-V_{CB} = 45\text{ V}$ at $-V_{CB} = 25\text{ V}$ | BC327 BC328 | $-I_{CBO}$ | - | - | 100 100 | nA |
| Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$ | BC327 BC328 | $-V_{(BR)CBO}$ | 50 30 | - - | - - | V |
| Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$ | BC327 BC328 | $-V_{(BR)CEO}$ | 45 25 | - - | - - | V |
| Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$ | | $-V_{(BR)EBO}$ | 5 | - | - | V |
| Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$ | | $-V_{CE(sat)}$ | - | - | 0.7 | V |
| Base Emitter On Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$ | | $-V_{BE(on)}$ | - | - | 1.2 | V |
| Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 50\text{ MHz}$ | | f_T | - | 100 | - | MHz |
| Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | | C_{CBO} | - | 12 | - | pF |



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103

ISO 14001:2004
Certificate No. 71116

ISO 9001:2000
Certificate No. 0506098

Dated : 27/12/2007

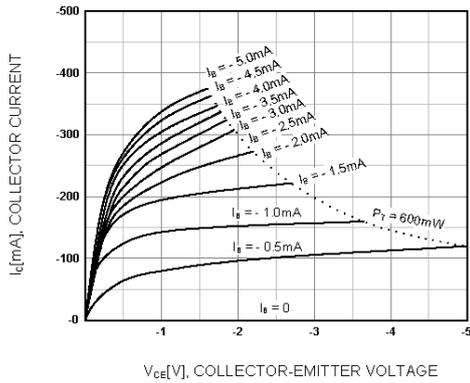


Figure 1. Static Characteristic

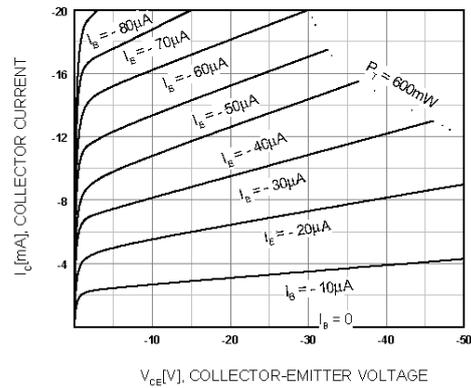


Figure 2. Static Characteristic

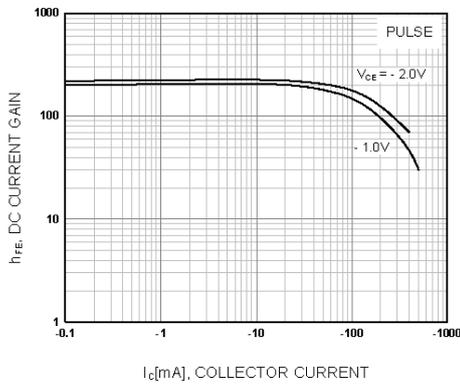


Figure 3. DC current Gain

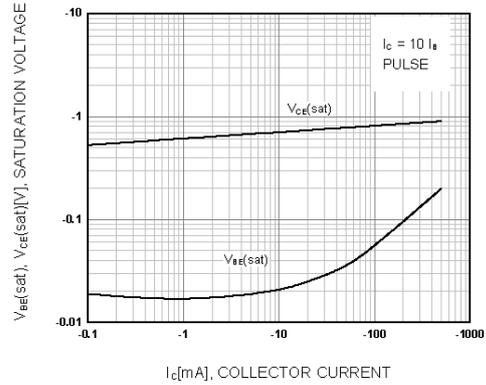


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

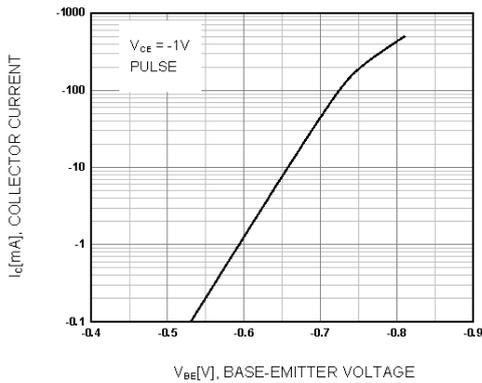


Figure 5. Base-Emitter On Voltage

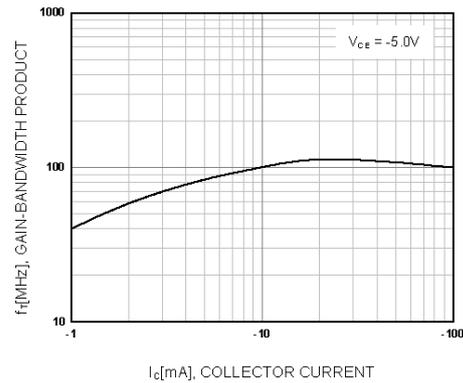
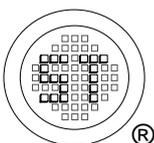


Figure 6. Gain Bandwidth Product



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